

In the Specification:

Please amend the specification per the substitute specification. A marked copy of the substitute specification showing changes thereto is included.

In the Drawings:

Please amend Figs. 3i and 3m per the proposed changes thereto submitted in red ink.

In the Claims:

1. Please amend the claims as follows:

1. (Once Amended) A semiconductor arrangement comprising:

- a substrate having a substrate layer (13) with an upper surface and a lower surface, the substrate layer (13) being of a first conductivity type;
- a first buried layer (12) in the substrate, extending along said lower surface below a first portion of said upper surface of said substrate layer (13), and a second buried layer (12) in the substrate, extending along said lower surface below a second portion of said upper surface of said substrate layer (13);
- a first diffusion region (26) in said first portion of said substrate layer (13), being of a second conductivity type opposite to said first conductivity type and having a first areal size for defining a first breakdown voltage;
- a second diffusion region (45) in said second portion of said substrate layer (13), being of said second conductivity type and having a second areal size for defining a second breakdown voltage; and